

FCMT180N65S3

Power MOSFET, N-Channel, SUPERFET[®] III, Easy Drive, 650 V, 17 A, 180 mΩ

Description

SUPERFET III MOSFET is ON Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate.

Consequently, SUPERFET III MOSFET Easy-drive series helps manage EMI issues and allows for easier design implementation.

The Power88 package is an ultra-slim surface-mount package (1 mm high) with a low profile and small footprint (8x8 mm²). SUPERFET III MOSFET in a Power88 package offers excellent switching performance due to lower parasitic source inductance and separated power and drive sources. Power88 offers Moisture Sensitivity Level 1 (MSL 1).

Features

- 700 V @ T_J = 150 °C
- Typ R_{DS(on)} = 152 mΩ
- Ultra Low Gate Charge (Typ. Q_g = 33 nC)
- Low Effective Output Capacitance (Typ. C_{oss(eff.)} = 305 pF)
- 100% Avalanche Tested
- These Devices are Pb-Free and are RoHS Compliant

Applications

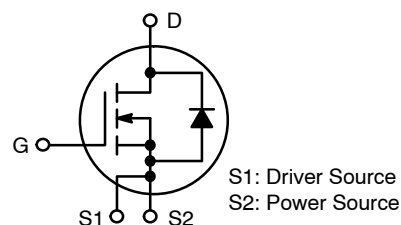
- Telecom / Server Power Supplies
- Industrial Power Supplies
- UPS / Solar
- Lighting / Charger / Adapter



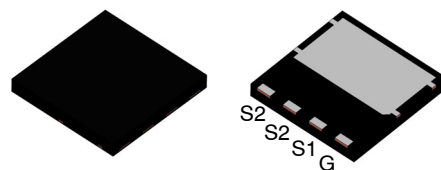
ON Semiconductor[®]

www.onsemi.com

V _{DSS}	R _{DS(on)} MAX	I _D MAX
650 V	180 mΩ @ 10 V	17 A

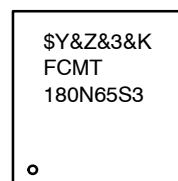


POWER MOSFET



Power88
PQFN4 8X8 2P
CASE 483AP

MARKING DIAGRAM



\$Y = ON Semiconductor Logo
&Z = Assembly Plant Code
&3 = Data Code (Year & Week)
&K = Lot Code
FCMT180N65S3 = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FCMT180N65S3

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, Unless otherwise specified)

Symbol	Parameter	Value	Unit
V _{DSS}	Drain to Source Voltage	650	V
V _{GSS}	Gate to Source Voltage	DC	±30
		AC (f > 1 Hz)	±30
I _D	Drain Current	Continuous (T _C = 25°C)	17
		Continuous (T _C = 100°C)	11
I _{DM}	Drain Current	Pulsed (Note 1)	42.5
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	80	mJ
I _{AS}	Avalanche Current (Note 2)	2.4	A
E _{AR}	Repetitive Avalanche Energy (Note 1)	1.39	mJ
dv/dt	MOSFET dv/dt	100	V/ns
	Peak Diode Recovery dv/dt (Note 3)	20	
P _D	Power Dissipation	(T _C = 25°C)	139
		Derate Above 25°C	1.11
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 s	300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. I_{AS} = 2.4 A, R_G = 25 Ω starting T_J = 25°C
3. I_{SD} ≤ 9 A, di/dt ≤ 200 A/μs, V_{DD} ≤ 400 V, starting T_J = 25°C

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
R _{θJC}	Thermal Resistance, Junction to Case, Max.	0.9	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient, Max. (Note 4)	45	

4. Device on 1 in² pad 2 oz copper pad on 1.5 x 1.5 in. board of FR-4 material.

ORDERING INFORMATION

Part Number	Top Marking	Package	Reel Size	Tape Width	Shipping†
FCMT180N65S3	FCMT180N65S3	Power88	13"	13.3 mm	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

FCMT180N65S3

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
--------	-----------	----------------	-----	-----	-----	------

OFF CHARACTERISTICS

BV _{DSS}	Drain to Source Breakdown Voltage	V _{GS} = 0 V, I _D = 1 mA, T _J = 25°C	650	–	–	V
		V _{GS} = 0 V, I _D = 1 mA, T _J = 150°C	700	–	–	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 1mA, referenced to 25°C	–	0.64	–	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 650 V, V _{GS} = 0 V	–	–	10	μA
		V _{DS} = 520 V, T _C = 125 °C	–	1.18	–	
I _{GSS}	Gate to Source Leakage Current	V _{GS} = ±30 V, V _{DS} = 0 V	–	–	±100	nA

ON CHARACTERISTICS

V _{GS(th)}	Gate Threshold Voltage	V _{GS} = V _{DS} , I _D = 1.8 mA	2.5	–	4.5	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 8.5 A	–	152	180	mΩ
g _{FS}	Forward Transconductance	V _{DS} = 20 V, I _D = 8.5 A	–	11	–	S

DYNAMIC CHARACTERISTICS

C _{iss}	Input Capacitance	V _{DS} = 400 V, V _{GS} = 0 V, f = 1 MHz	–	1350	–	pF
C _{oss}	Output Capacitance		–	30	–	pF
C _{oss(eff.)}	Effective Output Capacitance	V _{DS} = 0 V to 400 V, V _{GS} = 0 V	–	305	–	pF
C _{oss(er.)}	Energy Related Output Capacitance	V _{DS} = 0 V to 400 V, V _{GS} = 0 V	–	42	–	pF
Q _{g(tot)}	Total Gate Charge at 10 V	V _{DS} = 400 V, I _D = 8.5 A, V _{GS} = 10 V (Note 5)	–	33	–	nC
Q _{gs}	Gate to Source Gate Charge		–	8	–	nC
Q _{gd}	Gate to Drain “Miller” Charge		–	14	–	nC
ESR	Equivalent Series Resistance	f = 1 MHz	–	0.5	–	Ω

SWITCHING CHARACTERISTICS

t _{d(on)}	Turn-On Delay Time	V _{DD} = 400 V, I _D = 8.5 A, V _{GS} = 10 V, R _{GEN} = 4.7 Ω (Note 5)	–	17	–	ns
t _r	Rise Time		–	16	–	ns
t _{d(off)}	Turn-Off Delay Time		–	43	–	ns
t _f	Fall Time		–	6	–	ns

SOURCE-DRAIN DIODE CHARACTERISTICS

I _S	Maximum Continuous Source to Drain Diode Forward Current	–	–	17	A	
I _{SM}	Maximum Pulsed Source to Drain Diode Forward Current	–	–	42.5	A	
V _{SD}	Source to Drain Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 8.5 A	–	–	1.2	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 8.5 A, di _F /dt = 100 A/μs	–	290	–	ns
Q _{rr}	Reverse Recovery Charge		–	3.9	–	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Essentially independent of operating temperature typical characteristics.

TYPICAL PERFORMANCE CHARACTERISTICS

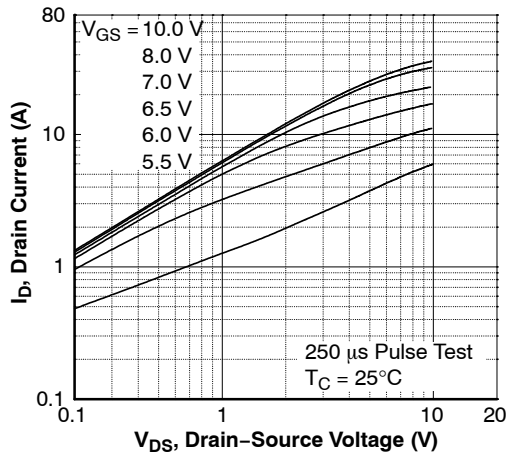


Figure 1. On-Region Characteristics

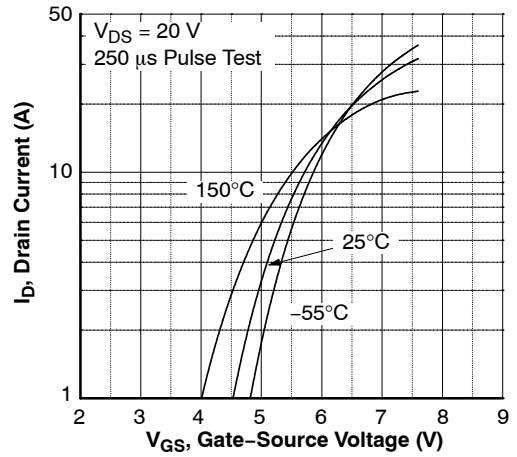


Figure 2. Transfer Characteristics

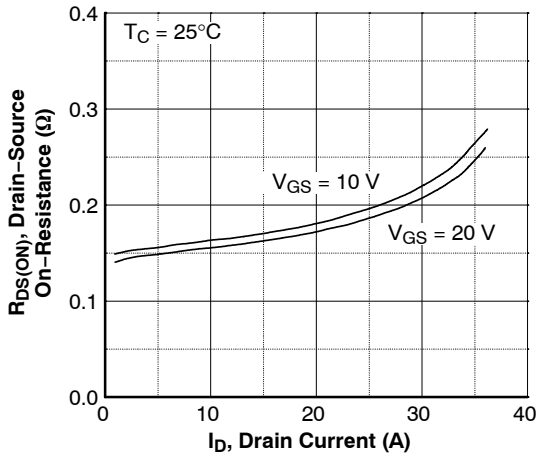


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

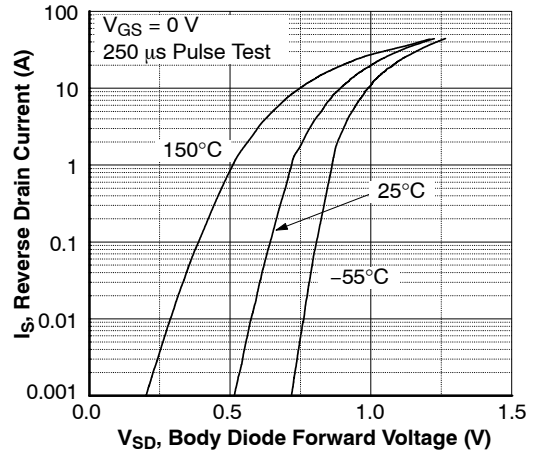


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

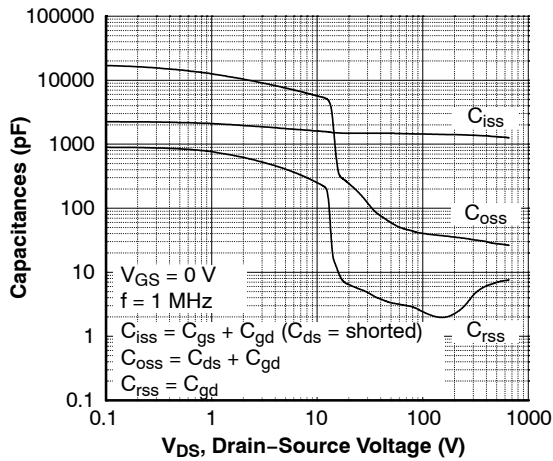


Figure 5. Capacitance Characteristics

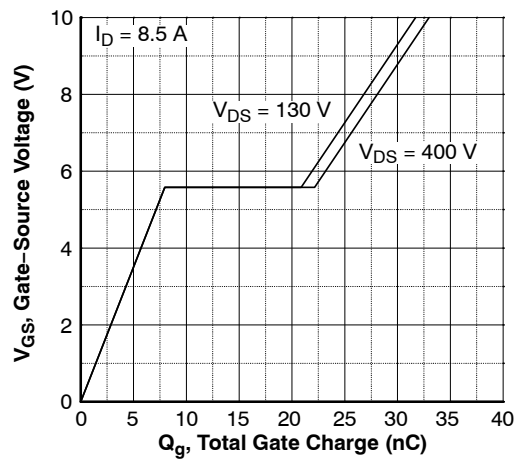


Figure 6. Gate Charge Characteristics

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

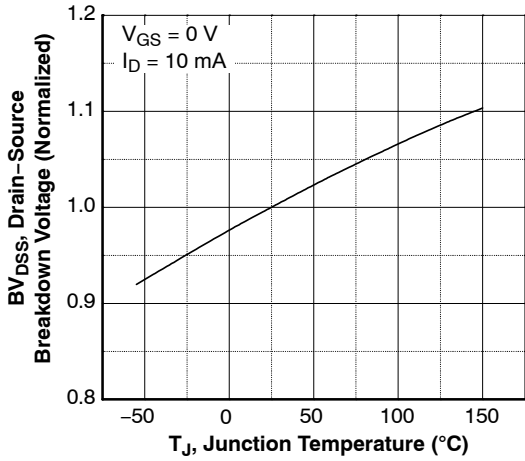


Figure 7. Breakdown Voltage Variation vs. Temperature

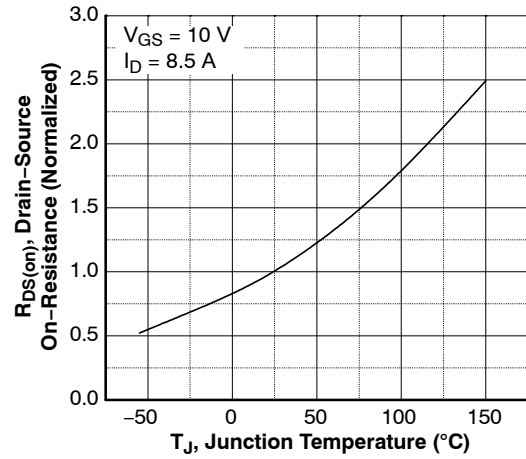


Figure 8. On-Resistance Variation vs. Temperature

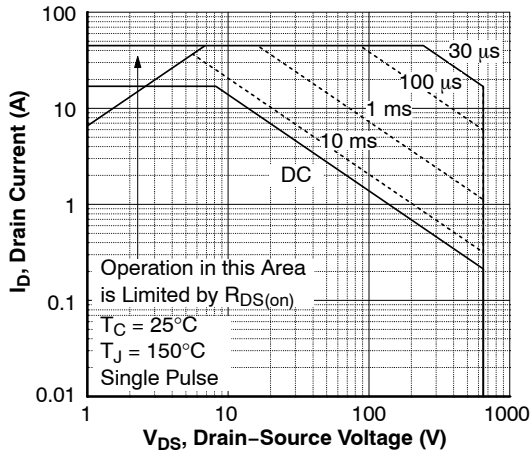


Figure 9. Maximum Safe Operating Area

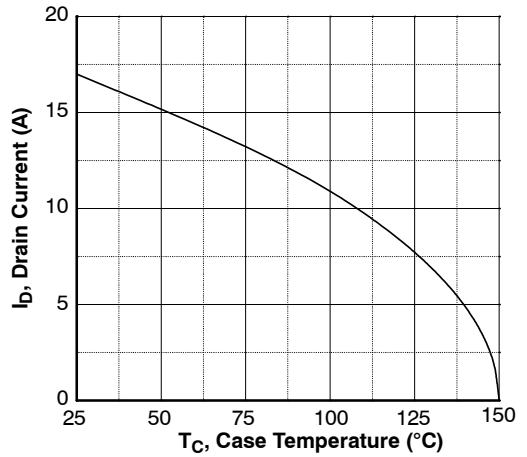


Figure 10. Maximum Drain Current vs. Case Temperature

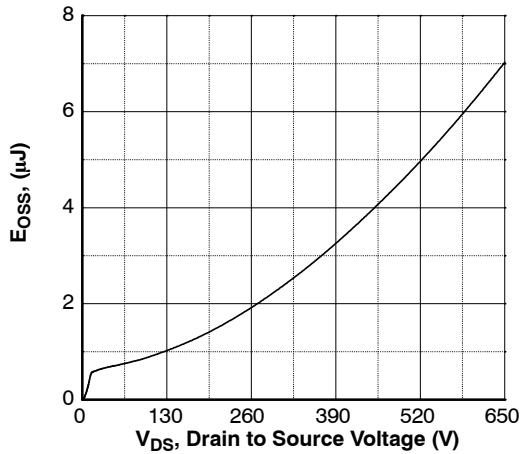


Figure 11. E_{OSS} vs. Drain to Source Voltage

FCMT180N65S3

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

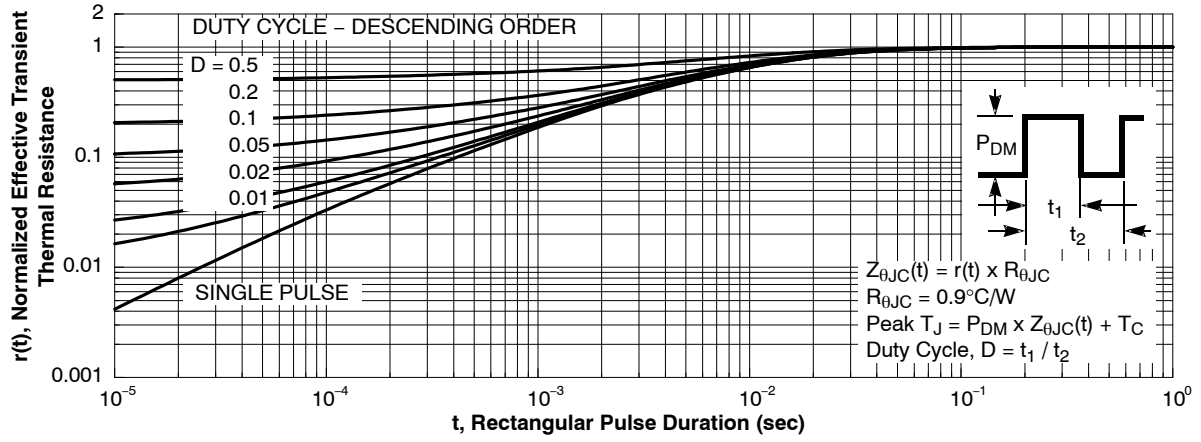


Figure 12. Transient Thermal Response Curve

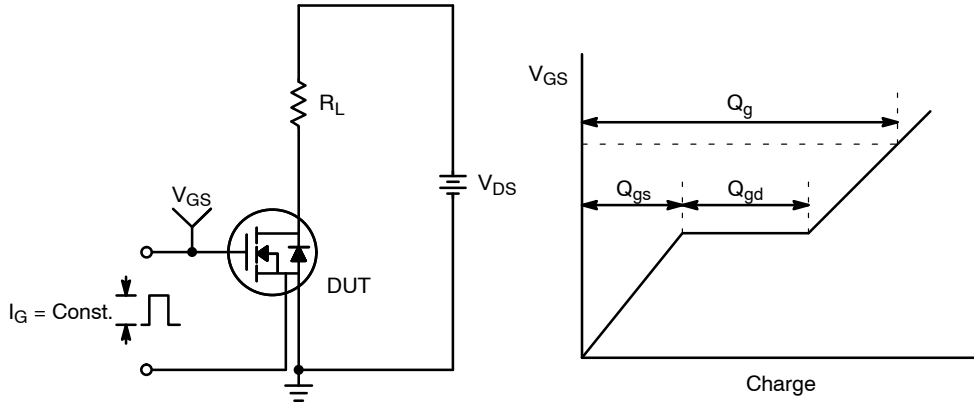


Figure 13. Gate Charge Test Circuit & Waveform

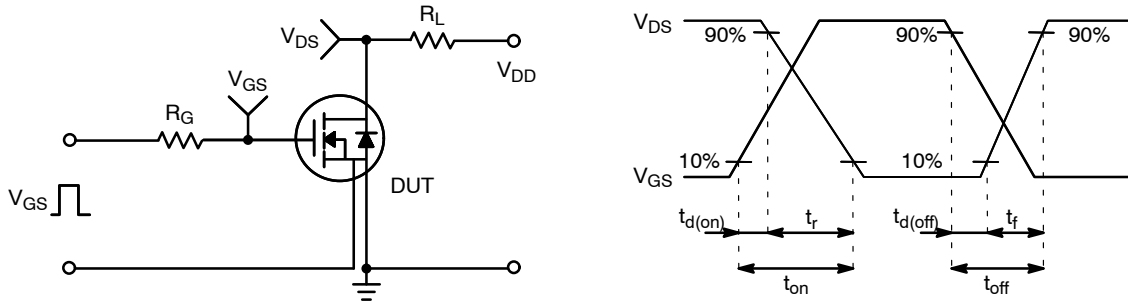


Figure 14. Resistive Switching Test Circuit & Waveforms

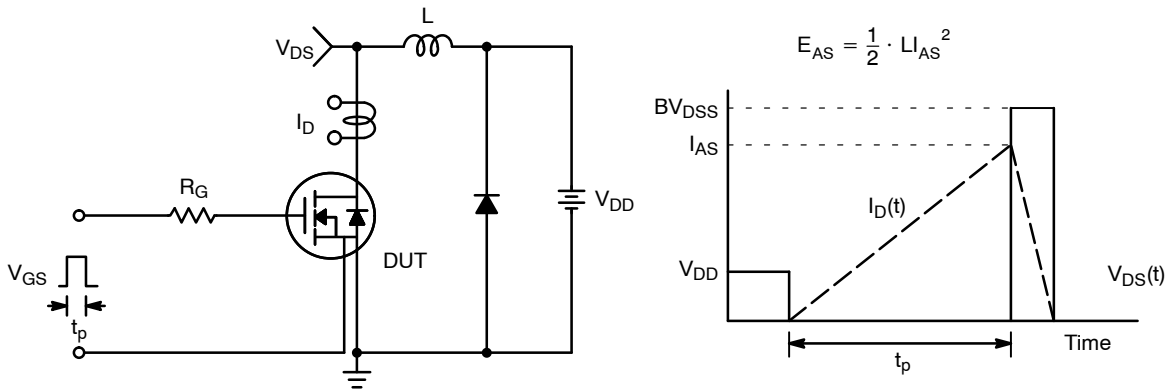


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

FCMT180N65S3

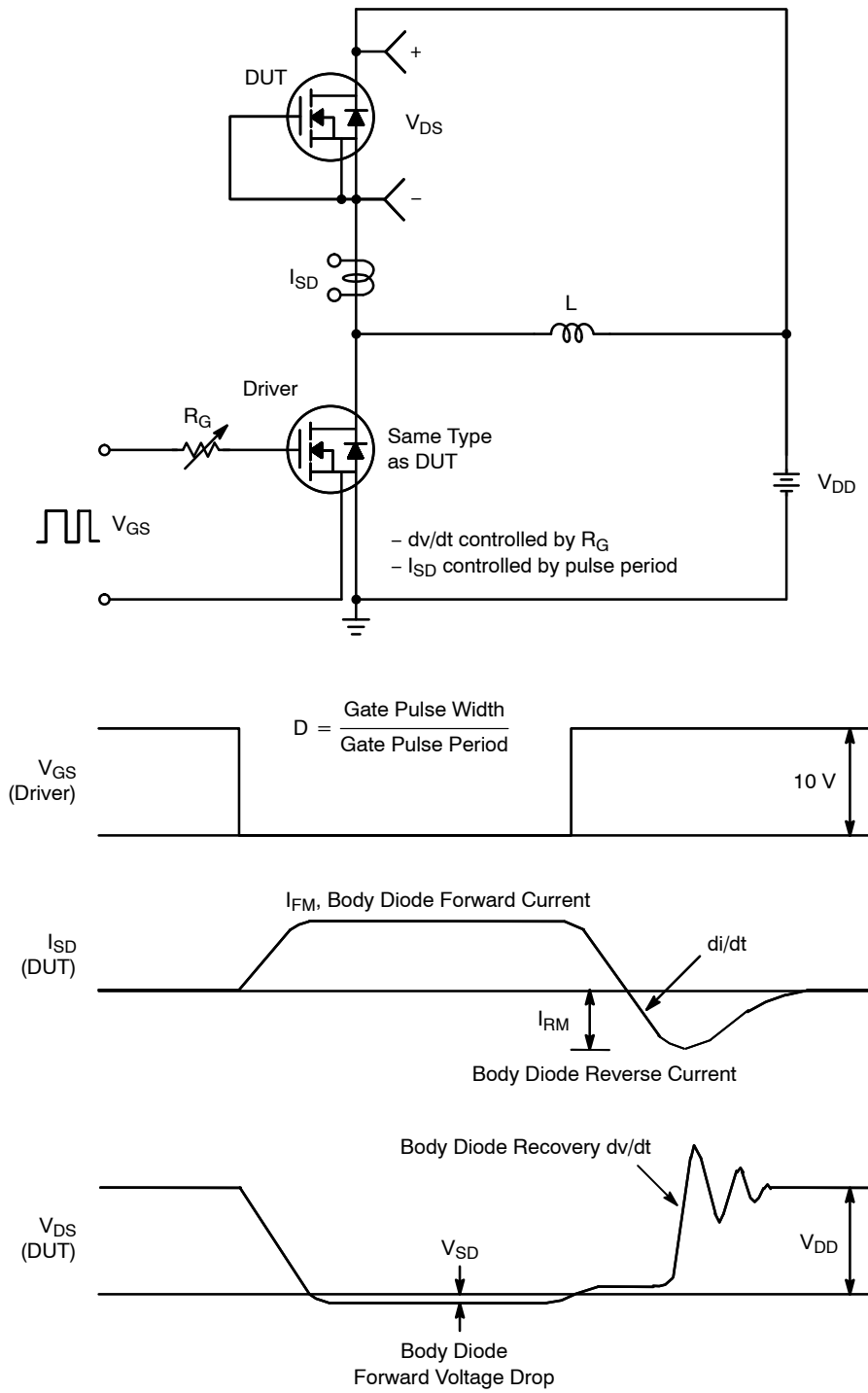


Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms

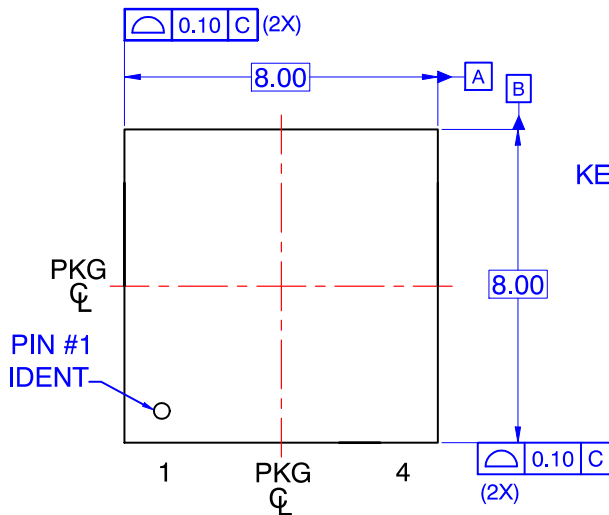
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

ON Semiconductor®

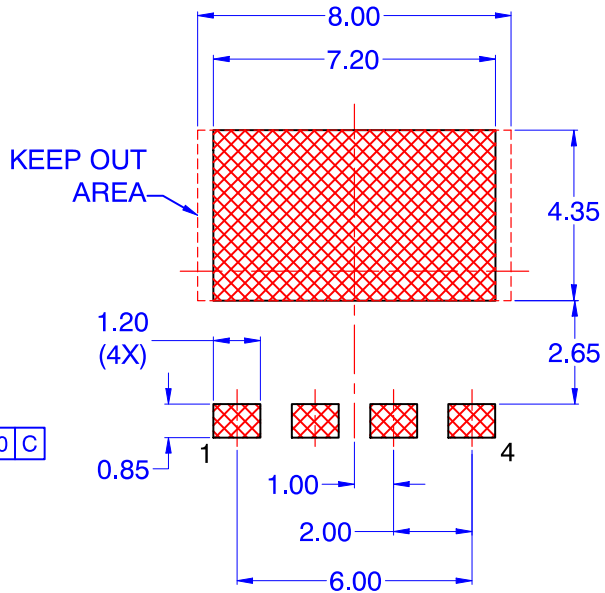


PQFN4 8X8, 2P
CASE 483AP
ISSUE O

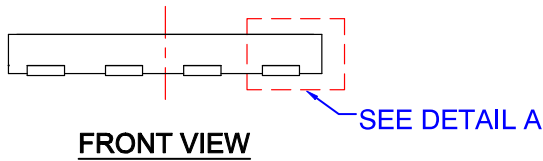
DATE 30 SEP 2016



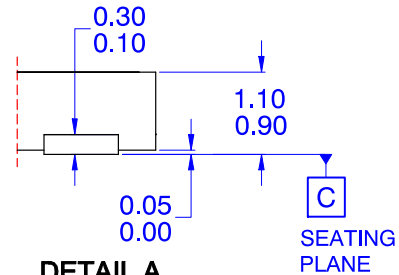
TOP VIEW



LAND PATTERN RECOMMENDATION

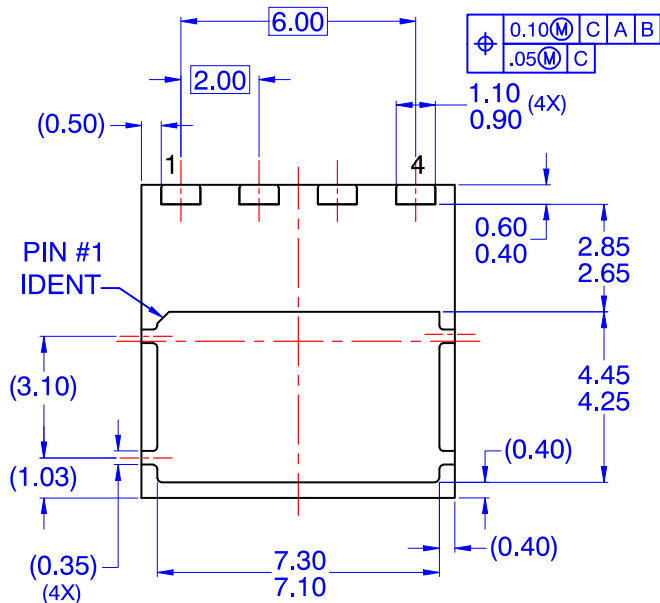


FRONT VIEW



DETAIL A

SCALE: 2X



BOTTOM VIEW

- NOTES: UNLESS OTHERWISE SPECIFIED
- A) THIS PACKAGE IS NOT PRESENTLY REGISTERED WITH ANY STANDARDS COMMITTEE.
 - B) DIMENSIONS ARE INCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR PROTRUSIONS.
 - C) ALL DIMENSIONS ARE IN MILLIMETERS.
 - D) DRAWING CONFORMS TO ASME Y14.5M-1994.

DOCUMENT NUMBER:	98AON13664G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
STATUS:	ON SEMICONDUCTOR STANDARD	
NEW STANDARD:		
DESCRIPTION:	PQFN4 8X8, 2P	PAGE 1 OF 2

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910

ON Semiconductor Website: www.onsemi.com

Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local
Sales Representative